Certificate Number: Q10561

Certificate Number: E17276

BAS16WS

SMALL SIGNAL DIODES

PRV : 100 Volts
Io : 250 mA

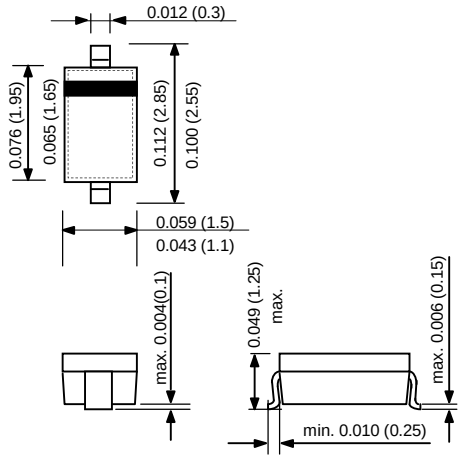
FEATURES :

* Silicon Epitaxial Planar Diode
* Fast switching diodes.
* Pb / RoHS Free

MECHANICAL DATA :

* Case : SOD-323 plastic Case
* Weight : approx. 0.004 g

SOD-323



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	75	V
Peak Reverse Voltage	V_{RM}	100	V
Rectified Current (Continuous)	$I_{F(AV)}$	250	mA
Surge Forward Current at t = 1 s and Tj = 25 °C	I_{FSM}	500	mA
Power Dissipation at T_{amb} = 25 °C	P_{tot}	200 [1)]	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	T_S	-65 to + 150	°C

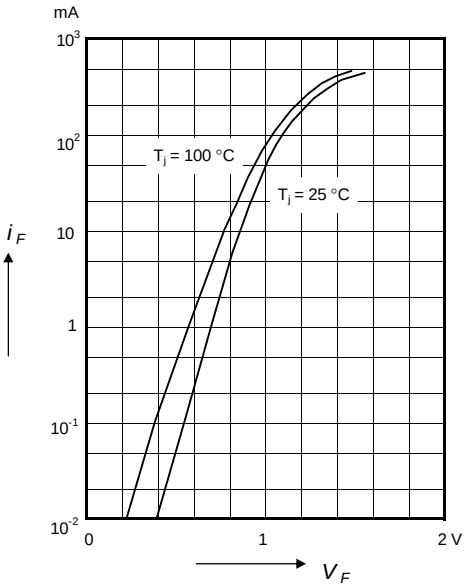
ELECTRICAL CHARACTERISTICS (Rating at Tj = 25 °C unless otherwise specified)

Parameter		Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at I_F = 50 mA		V_F	-	-	1	V
Leakage Current	at V_R=25 V, Tj=150°C	I_R	-	-	30	nA
	at V_R = 75 V	I_R	-	-	1	µA
	at V_R=75 V, Tj=150°C	I_R	-	-	50	µA
Capacitance at V_F = V_R = 0 V		C_{tot}	-	-	4	pF
Reverse Recovery Time from I_F = 10 mA to I_R = 10 mA, I_R = 6 V, R_L = 100 Ω		Trr	-	-	6	ns
Thermal Resistance Junction to Ambient Air		R_{thJA}	-	-	650 [1)]	°C/W

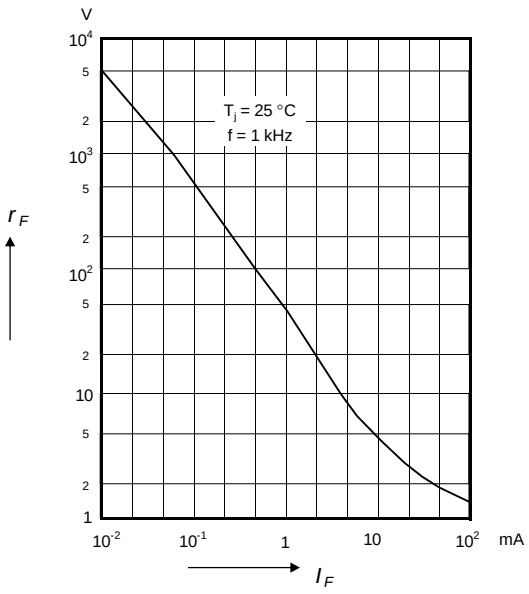
Note : 1) Valid provided that electrodes are kept at ambient temperature

RATINGS AND CHARACTERISTIC CURVES (BAS16WS)

Forward charecteristics

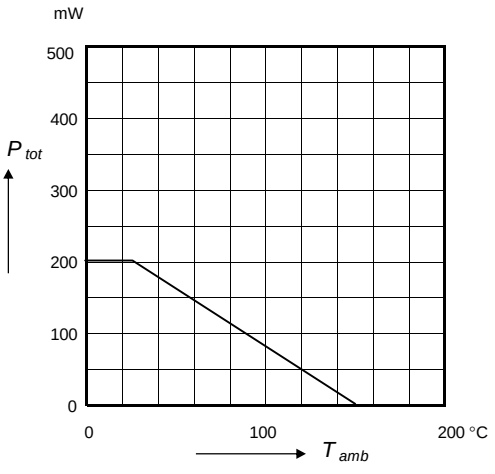


Dynamic forward resistance versus forward current



Admissible power dissipation versus ambient temperture

For conditions, see footnote in table "Absolute Maximum Ratings"



Relative capacitance versus reverse voltage